

MJE15028, MJE15030 (NPN) MJE15029, MJE15031 (PNP)

Preferred Device

Complementary Silicon Plastic Power Transistors

These devices are designed for use as high-frequency drivers in audio amplifiers.

Features

- DC Current Gain Specified to 4.0 Amperes
 $h_{FE} = 40$ (Min) @ $I_C = 3.0$ Adc
 $= 20$ (Min) @ $I_C = 4.0$ Adc
- Collector-Emitter Sustaining Voltage –
 $V_{CEO(sus)} = 120$ Vdc (Min); MJE15028, MJE15029
 $= 150$ Vdc (Min); MJE15030, MJE15031
- High Current Gain – Bandwidth Product
 $f_T = 30$ MHz (Min) @ $I_C = 500$ mAAdc
- TO-220AB Compact Package
- Pb-Free Packages are Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage MJE15028, MJE15029 MJE15030, MJE15031	V_{CEO}	120 150	Vdc
Collector-Base Voltage MJE15028, MJE15029 MJE15030, MJE15031	V_{CB}	120 150	Vdc
Emitter-Base Voltage	V_{EB}	5.0	Vdc
Collector Current – Continuous – Peak	I_C I_{CM}	8.0 16	Adc
Base Current	I_B	2.0	Adc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	50 0.40	W W/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	2.0 0.016	W W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristics	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	2.5	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62.5	$^\circ\text{C}/\text{W}$

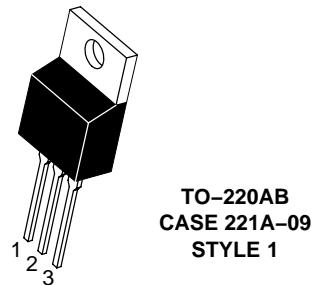
Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

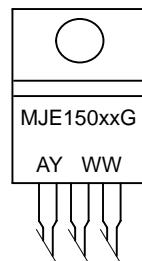


ON Semiconductor®

8 AMPERE POWER TRANSISTORS COMPLEMENTARY SILICON 120-150 VOLTS, 50 WATTS



MARKING DIAGRAM



MJE150xx = Device Code
x = 28, 29, 30, or 31
G = Pb-Free Package
A = Assembly Location
Y = Year
WW = Work Week

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

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ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Sustaining Voltage (Note 1) ($I_C = 10 \text{ mA}_\text{dc}$, $I_B = 0$)	$V_{CEO(\text{sus})}$	120 150	— —	Vdc
Collector Cutoff Current ($V_{CE} = 120 \text{ Vdc}$, $I_B = 0$) ($V_{CE} = 150 \text{ Vdc}$, $I_B = 0$)	I_{CEO}	— —	0.1 0.1	mA_dc
Collector Cutoff Current ($V_{CB} = 120 \text{ Vdc}$, $I_E = 0$) ($V_{CB} = 150 \text{ Vdc}$, $I_E = 0$)	I_{CBO}	— —	10 10	μA_dc
Emitter Cutoff Current ($V_{BE} = 5.0 \text{ Vdc}$, $I_C = 0$)	I_{EBO}	—	10	μA_dc
ON CHARACTERISTICS (Note 1)				
DC Current Gain ($I_C = 0.1 \text{ Adc}$, $V_{CE} = 2.0 \text{ Vdc}$) ($I_C = 2.0 \text{ Adc}$, $V_{CE} = 2.0 \text{ Vdc}$) ($I_C = 3.0 \text{ Adc}$, $V_{CE} = 2.0 \text{ Vdc}$) ($I_C = 4.0 \text{ Adc}$, $V_{CE} = 2.0 \text{ Vdc}$)	h_{FE}	40 40 40 20	— — — —	—
DC Current Gain Linearity (V_{CE} From 2.0 V to 20 V, I_C From 0.1 A to 3 A) (NPN to PNP)	h_{FE}	Typ 2 3		
Collector-Emitter Saturation Voltage ($I_C = 1.0 \text{ Adc}$, $I_B = 0.1 \text{ Adc}$)	$V_{CE(\text{sat})}$	—	0.5	Vdc
Base-Emitter On Voltage ($I_C = 1.0 \text{ Adc}$, $V_{CE} = 2.0 \text{ Vdc}$)	$V_{BE(\text{on})}$	—	1.0	Vdc
DYNAMIC CHARACTERISTICS				
Current Gain – Bandwidth Product (Note 2) ($I_C = 500 \text{ mA}_\text{dc}$, $V_{CE} = 10 \text{ Vdc}$, $f_{\text{test}} = 10 \text{ MHz}$)	f_T	30	—	MHz

1. Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2.0\%$.

2. $f_T = |h_{fe}| \cdot f_{\text{test}}$.

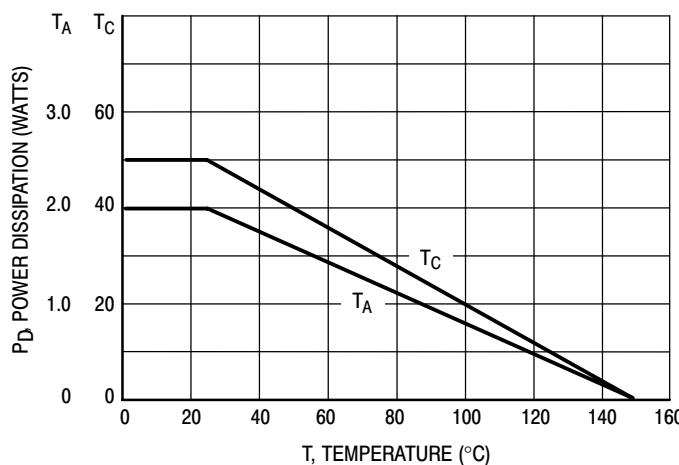


Figure 1. Power Derating

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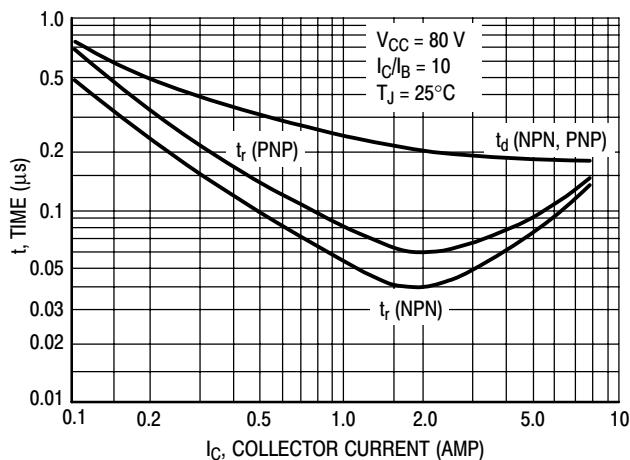


Figure 10. Turn-On Times

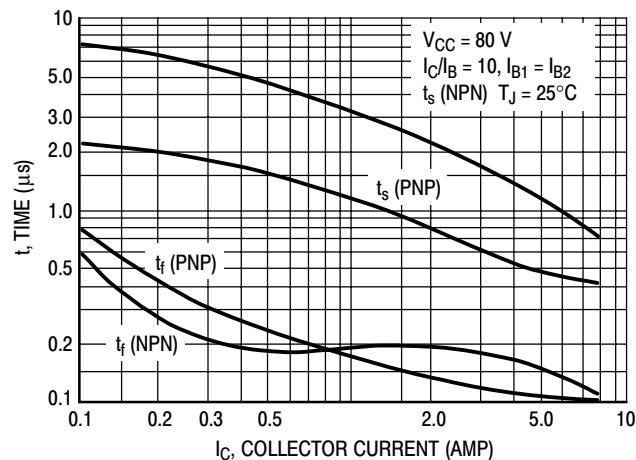


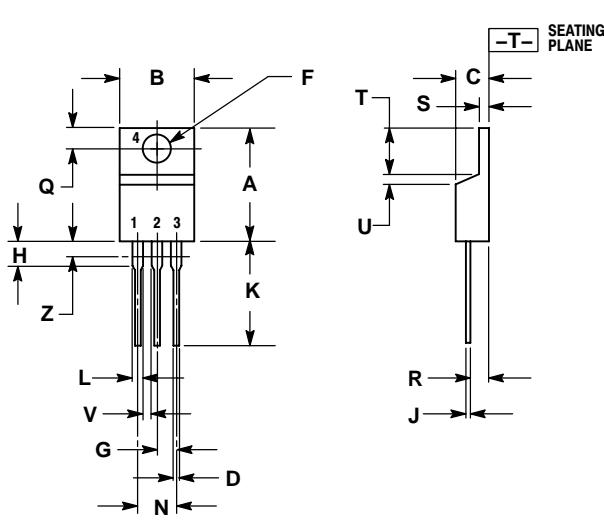
Figure 11. Turn-Off Times

ORDERING INFORMATION

Device	Package	Shipping
MJE15028	TO-220	50 Units / Rail
MJE15028G	TO-220 (Pb-Free)	50 Units / Rail
MJE15029	TO-220	50 Units / Rail
MJE15029G	TO-220 (Pb-Free)	50 Units / Rail
MJE15030	TO-220	50 Units / Rail
MJE15030G	TO-220 (Pb-Free)	50 Units / Rail
MJE15031	TO-220	50 Units / Rail
MJE15031G	TO-220 (Pb-Free)	50 Units / Rail

PACKAGE DIMENSIONS

TO-220AB
CASE 221A-09
ISSUE AA



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
J	0.018	0.025	0.46	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

- STYLE 1:
 PIN 1. BASE
 2. COLLECTOR
 3. Emitter
 4. COLLECTOR